

STTH5L04DEE

Turbo 2 ultrafast recovery diode

Datasheet - production data

Features

- Very low switching losses
- High frequency and high pulse current operation
- Low thermal resistance
- High junction temperature
- ECOPACK®2 compliant component

Description

The STTH5L04 series uses ST's new 400 V planar Pt doping technology. The STTH5L04 is specially suited for switching mode base drive and transistor circuits.

Packaged in PowerFLAT™, this device is intended for use in low profile applications.

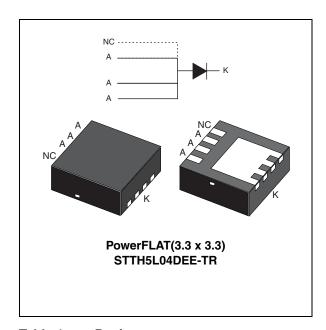


Table 1. Device summary

| Symbol | Value |
|-----------------------|--------|
| I _{F(AV)} | 5 A |
| V_{RRM} | 400 V |
| T _j (max) | 150 °C |
| V _F (typ) | 0.85 V |
| T _{RR} (typ) | 35 ns |

TM: PowerFLAT is a trademark of STMicroelectronics

Characteristics STTH5L04DEE

1 Characteristics

Table 2. Absolute ratings (limiting values $T_{amb} = 25$ °C unless otherwise specified)

| Symbol | Parameter | Value | Unit | |
|---------------------|--------------------------------------|-------------|------|---|
| V _{RRM} | Repetitive peak reverse voltage | 400 | V | |
| I _{F(RMS)} | Forward rms current | | 15 | Α |
| I _{F(AV)} | Average forward current | 5 | Α | |
| I _{FSM} | Surge non repetitive forward current | 60 | Α | |
| T _{stg} | Storage temperature range | -65 to +150 | °C | |
| T _j | Maximum operating junction tempera | 150 | °C | |

Table 3. Thermal resistance

| Symbol | Parameter | Value | Unit |
|----------------------|---|-------|------|
| R _{th(j-c)} | Junction to case | 4.5 | °C/W |
| R _{th(j-a)} | Junction to ambient on printed circuit board (with recommended footprint dimension, copper thickness = $35 \mu m$) | 250 | °C/W |

Table 4. Static electrical characteristics

| Symbol | Parameter | Test conditions | | Min. | Тур. | Max. | Unit |
|-------------------------------|----------------------|-------------------------|---------------------|------|------|------|------|
| I _R ⁽¹⁾ | Reverse leakage | T _j = 25 °C | $V_R = V_{RRM}$ | - | | 2.5 | μΑ |
| 'R' | current | T _j = 125 °C | VR - VRRM | - | 2.5 | 25 | μΑ |
| V _E ⁽²⁾ | Forward voltage drop | T _j = 25 °C | I _F = 5A | | 1.05 | 1.25 | V |
| v _E ., | Torward voilage drop | T _j = 150 °C | | - | 0.85 | 1.05 | V |

^{1.} Pulse test: $t_p = 5$ ms, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.85 \text{ x I}_{F(AV)} + 0.04 \text{ x I}_{F^{2}(RMS)}^{2}$$

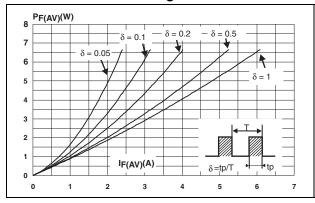
 Table 5.
 Dynamic electrical characteristics

| Symbol | Parameter | Test conditions | | | Тур. | Max. | Unit |
|---------------------|--------------------------|-------------------------|---|---|------|------|------|
| I _{RM} | Reverse recovery current | T _i = 125 °C | $T_j = 125 ^{\circ}\text{C}$ $I_F = 5\text{A}, V_R = 320 \text{V},$ $dI_F/dt = -200 \text{A/}\mu\text{s}$ | | 8 | 11 | Α |
| S _{factor} | Softness factor | • | | | 0.7 | | |
| | Reverse recovery time | T _i = 25 °C | $I_F = 1A$, $V_R = 30 V$, $dI_F/dt = -50 A/\mu s$ | | 43 | 60 | ns |
| t _{rr} | neverse recovery time | 1 _j = 25 °C | $I_F = 1A$, $V_R = 30 V$, $dI_F/dt = -100 A/\mu s$ | - | 35 | 50 | 115 |
| t _{fr} | Forward recovery time | T _j = 25 °C | $T_j = 25 ^{\circ}\text{C}$ $I_F = 5 \text{A}, V_{FB} = 1.2 \text{V}$ | | | 110 | ns |
| V _{FP} | Forward recovery voltage | T _j = 25 °C | $dI_F/dt = 100 \text{ A/}\mu\text{s}$ | - | 2 | 3 | ٧ |

^{2.} Pulse test: $t_p = 380 \mu s$, $\delta < 2\%$

STTH5L04DEE Characteristics

Figure 1. Average forward power dissipation Figure 2. Forward voltage drop versus versus average forward current forward current



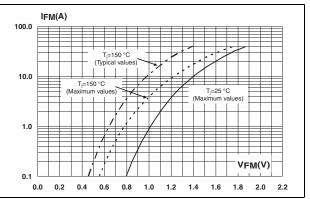
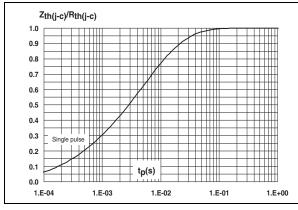


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl_F/dt (typical values)



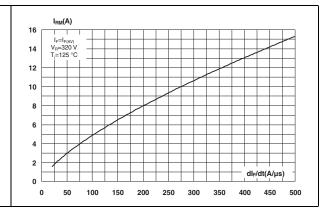
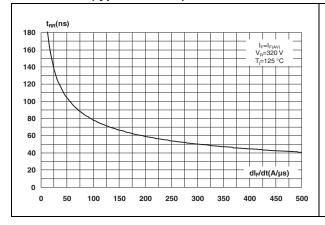
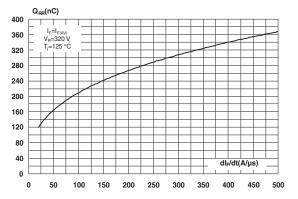


Figure 5. Reverse recovery time versus dl_F/dt Figure 6. (typical values)

Reverse recovery charges versus dl_F/dt (typical values)

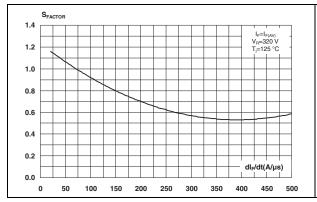




Characteristics STTH5L04DEE

Figure 7. Reverse recovery softness factor versus dl_E/dt (typical values)

Figure 8. Relative variation of dynamic parameters versus junction temperature



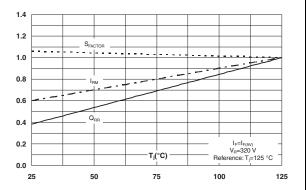
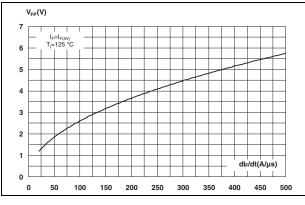


Figure 9. Transient peak forward voltage versus dl_F/dt (typical values)

Figure 10. Forward recovery time versus dl_F/dt (typical values)



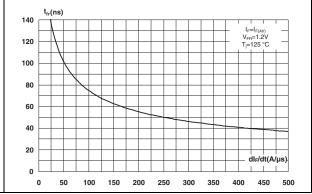
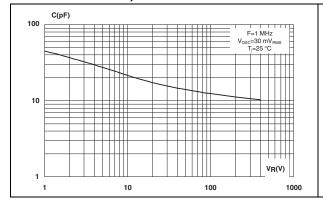
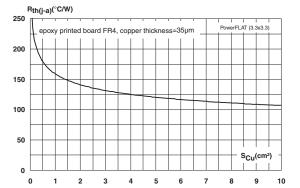


Figure 11. Junction capacitance versus reverse voltage applied (typical values)

Figure 12. Thermal resistance junction to ambient versus copper surface under tab





2 Package information

- Epoxy meets UL94,V0
- Lead-free package

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Figure 13. PowerFLAT (3.3 x 3.3) dimensions (definitions)

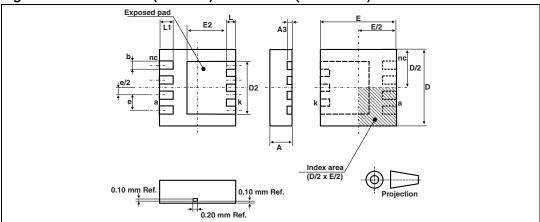
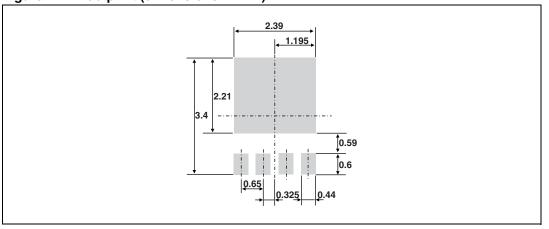


Table 6. PowerFLAT (3.3 x 3.3) dimensions (values)

| | Dimensions | | | | | |
|------|-------------|------|------|-------|-------|-------|
| Ref. | Millimeters | | | | | |
| | Min. | Тур. | Max. | Min. | Тур. | Max. |
| Α | 0.95 | | 1.0 | 0.037 | | 0.039 |
| А3 | | 0.2 | | | 0.008 | |
| b | 0.29 | 0.34 | 0.39 | 0.011 | 0.013 | 0.015 |
| D | 3.20 | 3.30 | 3.40 | 0.126 | 0.130 | 0.134 |
| D2 | 2.24 | 2.29 | 2.34 | 0.088 | 0.090 | 0.092 |
| E | 3.20 | 3.30 | 3.40 | 0.126 | 0.130 | 0.134 |
| E2 | 1.66 | 1.71 | 1.76 | 0.065 | 0.067 | 0.069 |
| е | | 0.65 | | | 0.026 | |
| L | | 0.40 | | | 0.016 | |
| L1 | 0.45 | 0.50 | 0.55 | 0.018 | 0.20 | 0.22 |

Package information STTH5L04DEE

Figure 14. Footprint (dimensions in mm)



3 Ordering information

Table 7. Ordering information

| Order code | Marking | Package | Weight | Base qty | Delivery mode |
|----------------|---------|--------------------------|--------|----------|---------------------------|
| STTH5L04DEE-TR | TH5L04 | PowerFLAT (3.3 x 3.3) | 34 mg | 3000 | Tape and reel 13" reel |

4 Revision history

Table 8. Document revision history

| Date | Revision | Changes |
|-------------|----------|--------------|
| 11-Sep-2012 | 1 | First issue. |

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